

## Silicon PNP Power Transistors

2SA634

## DESCRIPTION

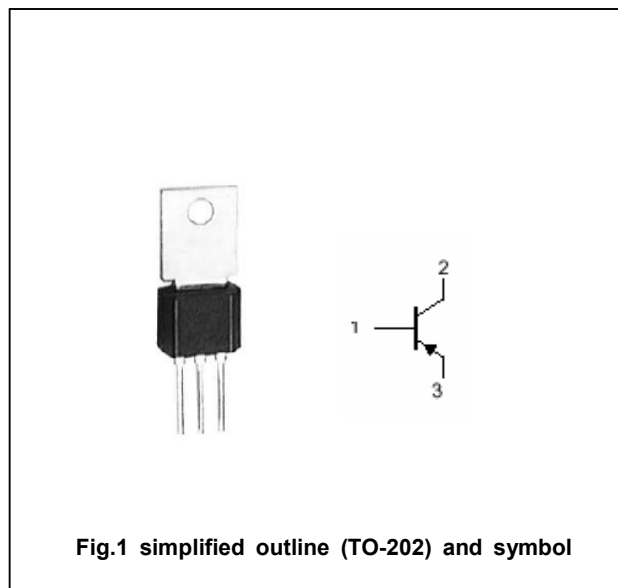
- With TO-202 package
- Complement to type 2SC1096
- High current capability

## APPLICATIONS

- Audio frequency power amplifier
- Low speed switching

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-40	V
$V_{CEO}$	Collector-emitter voltage	Open base	-30	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-3.0	A
$I_{CM}$	Collector current-peak		-6.0	A
$I_B$	Base current		-0.6	A
$P_T$	Total power dissipation	$T_a=25^\circ\text{C}$	1.2	W
		$T_C=25^\circ\text{C}$	10	
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

## Silicon PNP Power Transistors

## 2SA634

## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = -3.0A$ ; $I_B = -0.3A$		-0.7	-2.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C = -3.0A$ ; $I_B = -0.3A$		-1.1	-2.0	V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 10mA$ ; $I_B = 0$	-30			V
$h_{FE-1}$	DC current gain	$I_C = -20mA$ ; $V_{CE} = -5V$	20			
$h_{FE-2}$	DC current gain	$I_C = -1A$ ; $V_{CE} = -5V$	40		250	
$I_{CBO}$	Collector cut-off current	$V_{CB} = -30V$ ; $I_E = 0$			-1.0	$\mu A$
$I_{EBO}$	Emitter cut-off current	$V_{EB} = -3V$ ; $I_C = 0$			-1.0	$\mu A$
$C_{OB}$	Output capacitance	$I_E = 0$ ; $V_{CB} = -10V$ ; $f = 1MHz$		75		pF
$f_T$	Transition frequency	$I_C = -0.1A$ ; $V_{CE} = -5V$		55		MHz

◆  $h_{FE-2}$  Classifications

N	M	L	K
40-60	50-100	80-160	120-250

## Silicon PNP Power Transistors

2SA634

## PACKAGE OUTLINE

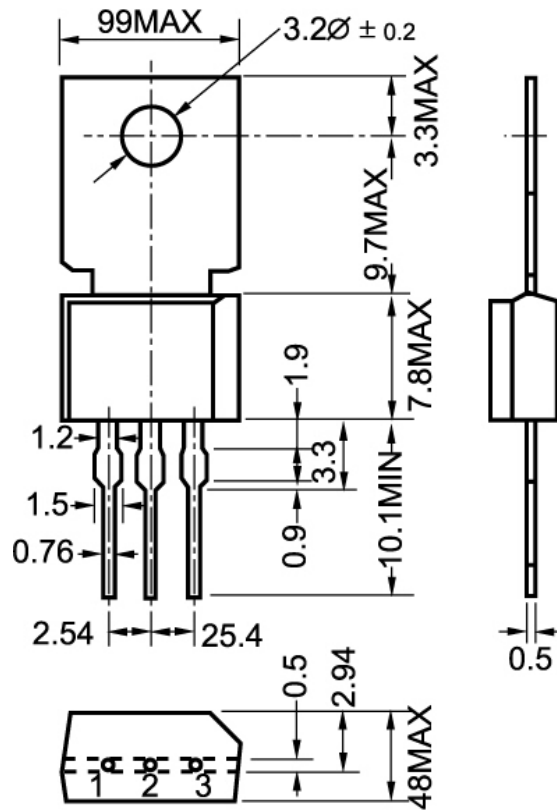


Fig.2 outline dimensions